

Is Now Part of



# **ON Semiconductor**®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lange of the applicatio customer's to unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the



## FDB12N50F N-Channel UniFET<sup>TM</sup> FRFET<sup>®</sup> MOSFET 500 V, 11.5 A, 700 m $\Omega$

### Features

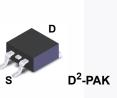
- $R_{DS(on)}$  = 590 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V, I<sub>D</sub> = 6 A
- Low Gate Charge (Typ. 21 nC)
- Low C<sub>rss</sub> (Typ. 11 pF)
- 100% Avalanche Tested
- Improve dv/dt Capability
- RoHS Compliant

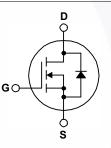
### Applications

- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET<sup>®</sup> MOSFET has been enhanced by lifetime control. Its t<sub>rr</sub> is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp balasts.





### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FDB12N50FTM_WS	Unit
V <sub>DSS</sub>	Drain to Source Voltage		500	V	
V <sub>GSS</sub>	Gate to Source Voltage		±30	V	
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		11.5	А
		- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		6.9	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	46	А
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	456	mJ
I <sub>AR</sub>	Avalanche Current (No		(Note 1)	11.5	А
E <sub>AR</sub>	Repetitive Avalanche Energy (Note		(Note 1)	16.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	20	V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25 <sup>o</sup> C)		165	W
		- Derate above 25°C		1.33	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

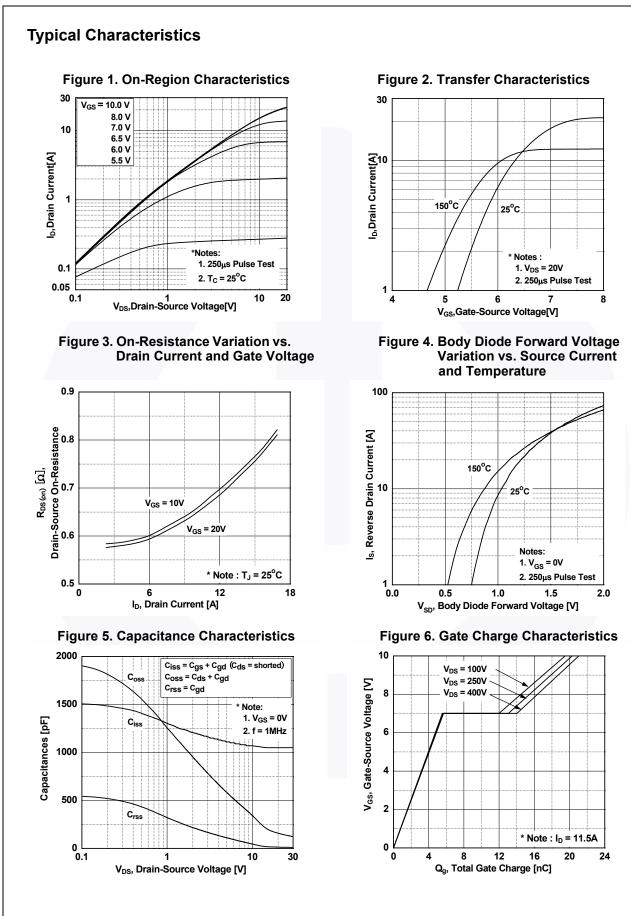
### Thermal Characteristics

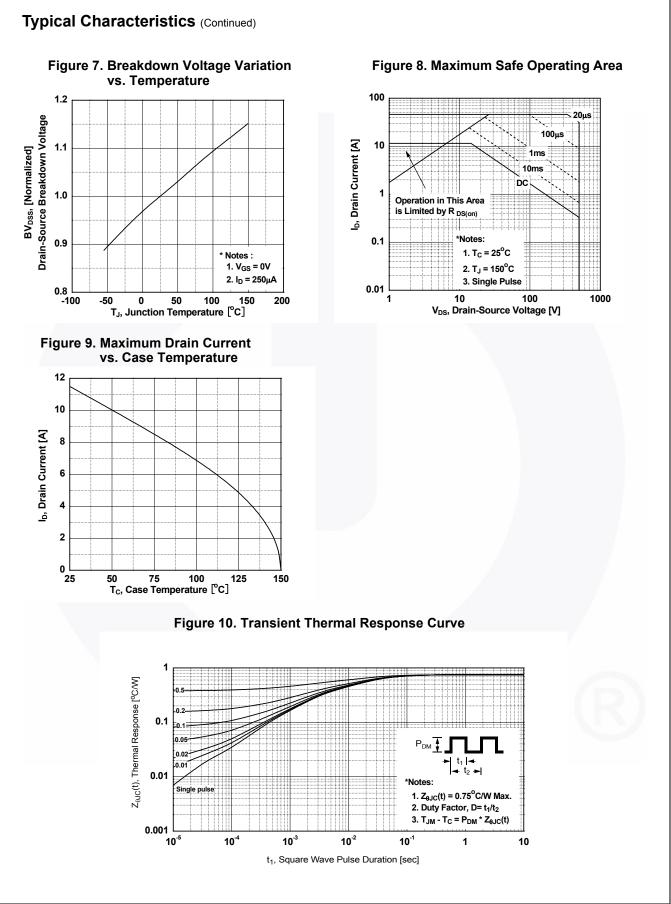
Symbol	Parameter	FQB12N50FTM_WS	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.75	
Р	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> pad of 2 oz copper), Max.	40	

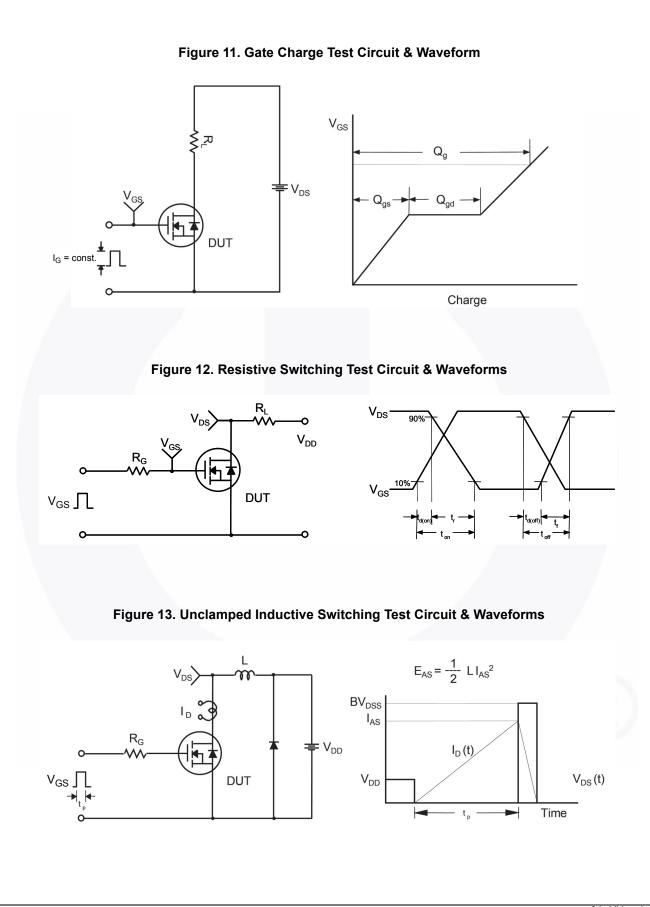
November 2013

FDB12N50FTM_WS	I <sub>D</sub> = 25	330mm e noted. <b>Test Conditions</b> 0μΑ, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25'	24mm Min.	Тур.	800 un Max.	its Unit
Parameter etics in to Source Breakdown Voltage akdown Voltage Temperature	I <sub>D</sub> = 25	Test Conditions		Тур.	Max.	Unit
tics in to Source Breakdown Voltage akdown Voltage Temperature				Тур.	Max.	Unit
in to Source Breakdown Voltage akdown Voltage Temperature		0μΑ, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25	°C 500			
akdown Voltage Temperature		0μΑ, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25	0C E00			
			500	-	-	V
efficient	10 = 25	$I_D = 250 \mu A$ , Referenced to $25^{\circ}C$		0.5	_	V/°C
	-	V <sub>DS</sub> = 500V, V <sub>GS</sub> = 0V			10	
o Gate Voltage Drain Current				-	-	μA
Gate to Body Leakage Current				-	±100	nA
					1	1
Gate Threshold Voltage				-		V
					0.7	Ω S
	VDS -	τον, η <sub>D</sub> - ολ	-	12	-	5
cteristics						
t Capacitance	\/	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1MHz		1050	1395	pF
out Capacitance				135	180	pF
			-			pF
-	Vpc =	V <sub>DS</sub> = 400V, I <sub>D</sub> = 11.5A V <sub>GS</sub> = 10V				nC nC
				-		
		(	Note 4)	9	-	nC
racteristics						
-On Delay Time			-	21	50	ns
-On Rise Time			-	45	100	ns
-Off Delay Time	R <sub>G</sub> = 2	$R_{G} = 25\Omega$		50	110	ns
o-Off Fall Time		(	Note 4) -	35	80	ns
oiode Characteristics						
	Diode Forwar	d Current	-	_	11.5	Α
			-	-	46	A
n to Source Diode Forward Voltage	e V <sub>GS</sub> = (	0V, I <sub>SD</sub> = 11.5A	-	-	1.5	V
erse Recovery Time		$V_{GS} = 0V, I_{SD} = 11.5A$ $dI_F/dt = 100A/\mu s$		134	-	ns
erse Recovery Charge	dI <sub>F</sub> /dt =			0.37	-	μΟ
	e to Body Leakage Current tics e Threshold Voltage ic Drain to Source On Resistance ward Transconductance exacteristics It Capacitance out Capacitance erse Transfer Capacitance I Gate Charge at 10V e to Source Gate Charge e to Drain "Miller" Charge cacteristics -On Delay Time -Off Delay Time -Off Pall Time Viode Characteristics imum Continuous Drain to Source Diode ros Source Diode Forward Voltage erse Recovery Time erse Recovery Charge	$V_{DS} = 4$ e to Body Leakage Current $V_{GS} = 3$ tics $V_{GS} = 3$ e Threshold Voltage $V_{GS} = 3$ ic Drain to Source On Resistance $V_{GS} = 3$ ward Transconductance $V_{DS} = 3$ ic Capacitance $V_{DS} = 3$ it Capacitance $V_{DS} = 3$ e to Source Gate Charge $V_{DS} = 3$ e to Source Gate Charge $V_{DS} = 3$ e to Drain "Miller" Charge $V_{DS} = 3$ racteristics $V_{DS} = 3$ -On Delay Time $V_{DD} = 3$ -On Rise Time $V_{DD} = 3$ -Off Delay Time $R_G = 2$ -Off Fall Time $R_G = 2$ viode Characteristics $R_G = 2$ imum Continuous Drain to Source Diode Forward Cun to Source Diode Forward Voltage $V_{GS} = 0$ erse Recovery Time $V_{GS} = 0$	VDS $= 400V, I_C = 125^{\circ}C$ a to Body Leakage Current $V_{GS} = \pm 30V, V_{DS} = 0V$ tics $V_{GS} = V_{DS}, I_D = 250\mu A$ a to Body Leakage Corrent $V_{GS} = V_{DS}, I_D = 250\mu A$ a to Drain to Source On Resistance $V_{GS} = 10V, I_D = 6A$ ward Transconductance $V_{DS} = 40V, I_D = 6A$ ward Transconductance $V_{DS} = 40V, I_D = 6A$ a to Capacitance $V_{DS} = 25V, V_{GS} = 0V$ a to Source Gate Charge $V_{DS} = 400V, I_D = 11.5A$ a to Source Gate Charge $V_{DS} = 400V, I_D = 11.5A$ a to Source Gate Charge $V_{DS} = 10V$ a to Source Gate Charge $V_{DS} = 250V, I_D = 11.5A$ a to Source Gate Charge $V_{DD} = 250V, I_D = 11.5A$ a to Drain "Miller" Charge $V_{DD} = 250V, I_D = 11.5A$ a coff Fall Time $V_{CS} = 0V, I_{SD} = 11.5A$ a coff Fall Time $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward CurrentImum Continuous Drain to Source Diode Forward Currenta to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ a to Source Diode Forwar	VDS400V, $\Gamma_{C} = 125^{\circ}C$ -a to Body Leakage Current $V_{GS} = \pm 30V, V_{DS} = 0V$ -ticsVDS $= 30V, V_{DS} = 0V$ -a Threshold Voltage $V_{GS} = V_{DS}, I_D = 250\mu A$ 3.0ic Drain to Source On Resistance $V_{GS} = 10V, I_D = 6A$ -ward Transconductance $V_{DS} = 40V, I_D = 6A$ -etceristics $V_{DS} = 40V, I_D = 6A$ -etceristics $f = 1MHz$ -etceractionce $f = 1MHz$ -I Gate Charge at $10V$ $V_{DS} = 400V, I_D = 11.5A$ -e to Drain "Miller" Charge $V_{CS} = 10V$ -e to Drain "Miller" Charge $V_{DS} = 250V, I_D = 11.5A$ Off Delay Time $V_{DD} = 250V, I_D = 11.5A$ Off Fall Time $V_{OS} = 25\Omega$ -ender Characteristicsinum Continuous Drain to Source Diode Forward Current-in to Source Diode Forward Current-in to Source Diode Forward Voltage $V_{GS} = 0V, I_{SD} = 11.5A$ -erse Recovery Time $V_{GS} = 0V, I_{SD} = 11.5A$ -erse Recovery Time $V_{GS} = 0V, I_{SD} = 11.5A$ -erse Recovery Charge $dI_F/dt = 100A/\mu_S$ -	VDS400V, I_C = 125°Ca to Body Leakage Current $V_{GS} = \pm 30V, V_{DS} = 0V$ ticsa Threshold Voltage $V_{GS} = V_{DS}, I_D = 250\mu$ A3.0-ic Drain to Source On Resistance $V_{GS} = 10V, I_D = 6A$ -0.59ward Transconductance $V_{DS} = 40V, I_D = 6A$ -12icteristics-1050ict Capacitance $V_{DS} = 25V, V_{GS} = 0V$ -135icteristics-111I Gate Charge at 10V-21a to Drain "Miller" Charge $V_{DS} = 400V, I_D = 11.5A$ -6vonce Gate Charge $V_{DS} = 10V$ -216-9racteristics66	VDS         = 4000', I_C = 125°C         -         -         100           e to Body Leakage Current         V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V         -         -         ±100           tics         -         -         -         ±100           a Threshold Voltage         V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250µA         3.0         -         5.0           ic Drain to Source On Resistance         V <sub>GS</sub> = 10V, I <sub>D</sub> = 6A         -         0.59         0.7           ward Transconductance         V <sub>DS</sub> = 40V, I <sub>D</sub> = 6A         -         12         -           etteristics         -         112         -         -           tCapacitance         V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V         -         135         180           erse Transfer Capacitance         F = 1MHz         -         11         17           I Gate Charge at 10V         V <sub>DS</sub> = 400V, I <sub>D</sub> = 11.5A         -         6         -           ot source Gate Charge         V <sub>DS</sub> = 400V, I <sub>D</sub> = 11.5A         -         6         -           -On Dialy Time         -         21         50         -         50         110           -On Rise Time         V <sub>DD</sub> = 250V, I <sub>D</sub> = 11.5A         -         45         100           -Off Eall Time         V <sub>CD</sub> = 250

FDB12N50F — N-Channel UniFET<sup>TM</sup> FRFET<sup>®</sup> MOSFET



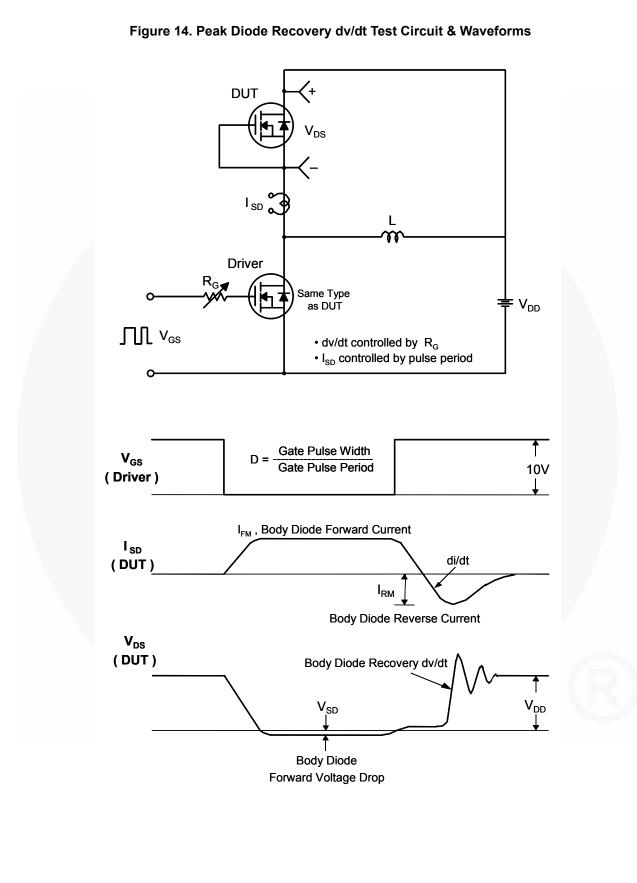


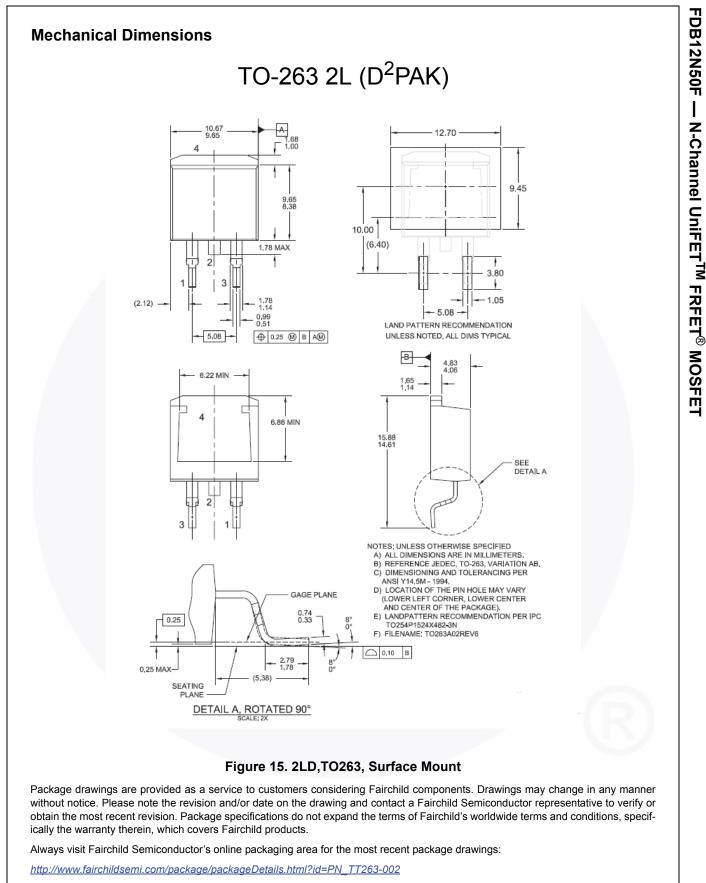


©2008 Fairchild Semiconductor Corporation FDB12N50F Rev. C1

www.fairchildsemi.com







**Dimension in Millimeters** 



SEMICONDUCTOR

#### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

intended to be an exhaustive list of	an such trauemarks.		
AccuPower™	F-PFS™		Sync-Lock™
AX-CAP <sup>®</sup> *	FRFET®	0	SYSTEM ®*
BitSiC™	Global Power Resource <sup>SM</sup>	PowerTrench <sup>®</sup>	GENERAL
Build it Now™	GreenBridge™	PowerXS™	TinyBoost <sup>®</sup>
CorePLUS™	Green FPS™	Programmable Active Droop™	TinyBuck <sup>®</sup>
CorePOWER™	Green FPS™ e-Series™	QFET®	TinyCalc™
CROSSVOLT™	Gmax™	QS™	TinyLogic®
CTL™	GTO™	Quiet Series™	TINYOPTO™
Current Transfer Logic™	IntelliMAX™	RapidConfigure™	TinyPower™
DEUXPEED®	ISOPLANAR™		TinyPWM™
Dual Cool™ EcoSPARK <sup>®</sup>	Marking Small Speakers Sound L and Better™	Saving our world, 1mW/W/kW at a time™	TinyWire™
Ecospark* EfficentMax™	MegaBuck™	Saving our world, Thiw/w/kw at a time ™ SignalWise™	TranSiC™
ESBC™	MICROCOUPLER™	SmartMax™	TriFault Detect™
2000	MicroFET™	SMART START™	TRUECURRENT®*
	MicroPak™	Solutions for Your Success™	µSerDes™
Fairchild <sup>®</sup>	MicroPak2™	SPM®	$\mathcal{M}$
Fairchild Semiconductor <sup>®</sup>	MillerDrive™	STEALTH™	/ Ser <mark>Des</mark> ™
FACT Quiet Series™	MotionMax™	SuperFET®	UHC®
FACT®	mWSaver®	SuperSOT™-3	Ultra FRFET™
FAST®	OptoHiT™	SuperSOT™-6	UniFET™
FastvCore™	OPTOLOGIC®	SuperSOT™-8	VCX™ ViewelNawr™
FETBench™	OPTOPLANAR®	SupreMOS®	VisualMax™ VoltagePlus™
FPS™		SyncFET™	XS™ XS™
			70

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS Definition of Term

Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC